ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	HIGH TOLERANCE TCR BALANCED HIGH CURRENT RESISTOR FOR RF CMOS AND RF SiGe BiCMOS APPLICATIONS AND CADENCED BASED HIERARCHICAL PARAMETERIZED CELL DESIGN KIT WITH TUNABLE TCR AND ESD RESISTOR BALLASTING FEATURE

Application Number :

Confirmation Number:

First Named Applicant: Ebenezer Eshun

Attorney Docket Number: BUR920030058US1

Art Unit:

Examiner:

Search string: (4668581 or 4866507 or 5045904 or 5106461 or 5182632 or 5203731 or 5275963 or 5872695 or 6379745 or 6436814).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	4668581	1987-05-26	Luc et al.			
	2	4866507	1989-09-12	Jacobs et al.			
	3	5045904	1991-09-03	Kobayashi et al.			
	4	5106461	1992-04-21	Volfson et al.			
	5	5182632	1993-01-26	Bechtel et al.			
	6	5203731	1993-04-20	Zimmerman			
	7	5275963	1994-01-04	Cederbaum et al.			
	8	5872695	1999-02-16	Fasano et al.			
	9	6379745	2002-04-30	Kydd et al.			
	10	6436814	2002-08-20	Horak et al.			

Signature

Examiner Name	Date
John Barry FROM	02/07/05